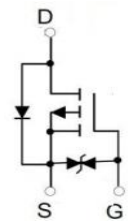




MT2301ET P-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	510m Ω @-4.5V	-0.75A
	750m Ω @-2.5V	
	960m Ω (TYP)@-1.8V	

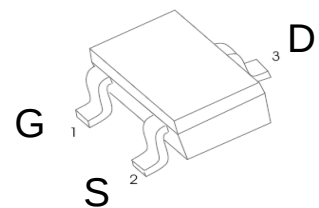


Feature

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive

Application

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics



SOT-523

MARKING: S1

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-0.75	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-1.2	A
Power Dissipation ⁽²⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$



MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

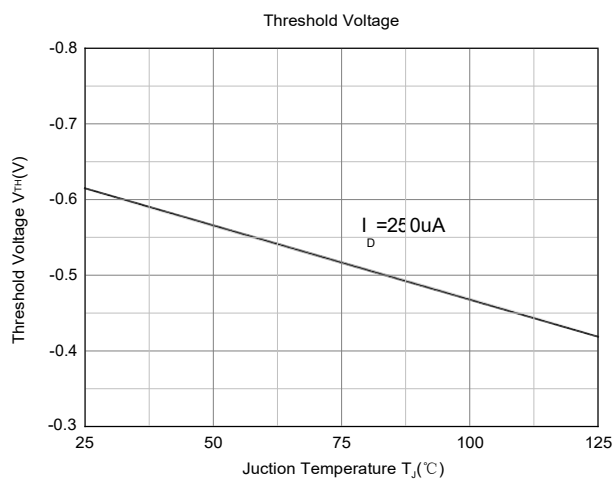
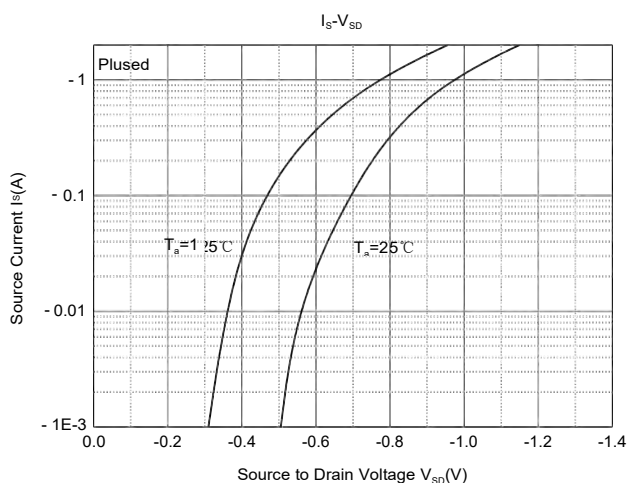
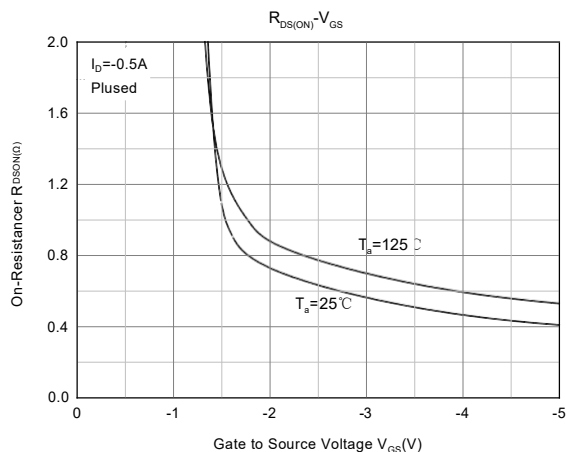
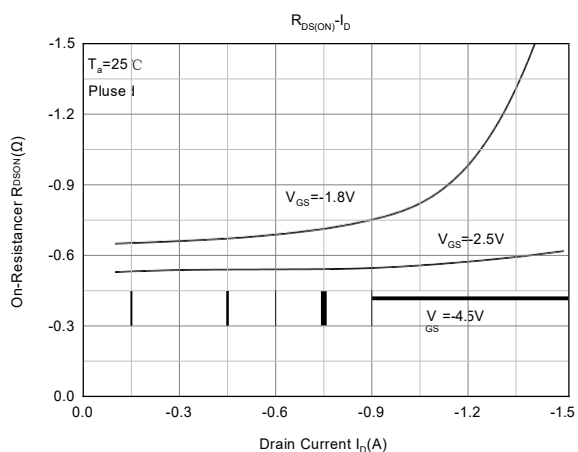
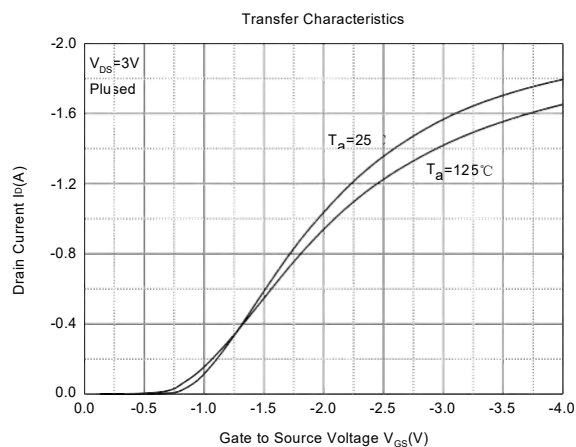
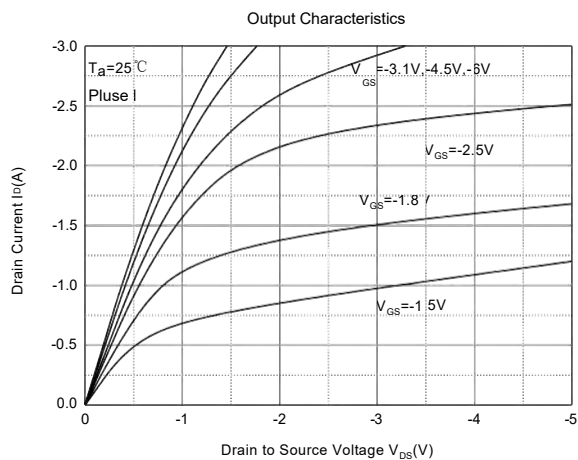
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.61	-1.1	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1A		420	510	mΩ
		V _{GS} =-2.5V, I _D =-0.8A		630	750	
		V _{GS} =-1.8V, I _D =-0.5A		960		
Forward tranconductance	g _{FS}	V _{DS} =-10V, I _D =-0.54A	0.8			S
Dynamic characteristics ⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =-16V,V _{GS} =0V,f =1MHz		113		pF
Output Capacitance	C _{oss}			15		
Reverse Transfer Capacitance	C _{rss}			9		
Switching Characteristics ⁽⁴⁾						
Turn-on delay time	t _{d(on)}	V _{DS} =-10V,I _D =-200mA, V _{GS} =-4.5V,R _G =10Ω		9		ns
Turn-on rise time	t _r			5.7		
Turn-off delay time	t _{d(off)}			32.6		
Turn-off fall time	t _f			20.3		
Source-Drain Diode characteristics						
Diode forward voltage ⁽³⁾	V _{DS}	I _S =-0.5A, V _{GS} = 0V			-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_a=25℃.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.
4. These parameters have no way to verify.

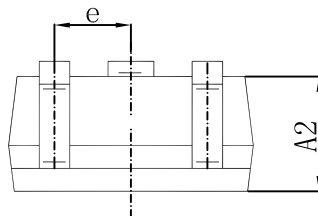
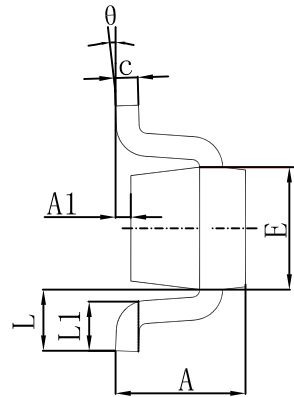
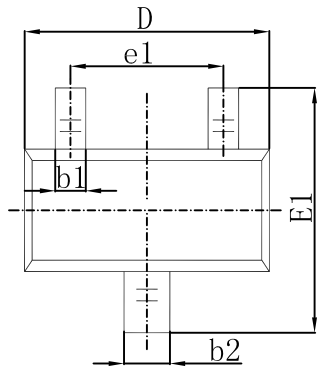


Typical Electrical and Thermal Characteristics



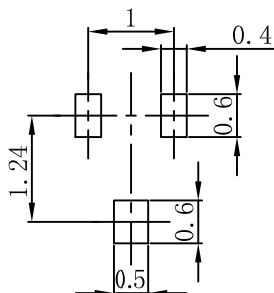


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.